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SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)		ATTY. DOCKET NO. <b>071971-0388</b>		SERIAL NO. <b>Not yet assigned</b>  <b>10/553628</b>	
		APPLICANT <b>Masao UCHIDA, et al.</b>			
		FILING DATE <b>October 19, 2005</b>		GROUP 2814 <b>Not yet assigned</b>	

  

U.S. PATENT DOCUMENTS					
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) of country	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Mbh		US 5977564 A	11/19/99	Kobayashi et al.	Corresponds to JP 10-321854 A
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code(s)-Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
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Mbh		JP 2003-234301 A	08-22-2003	Matsushita Electric Industrial Co., Ltd.	Corresponds to US 2003/0080384 A1		
Mbh		JP 2003-209251 A	07-25-03	Japan Atomic Energy Research Institute			
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
Mbh		G.Y. CHUNG, et al., "Improved Invention Channel Mobility for 4H-SiC MOSFETs Following High Temperature Anneals in Nitric Oxide," Electron Device Letters, April 2001, pp 176-178, Vol 22, No. 4, IEEE

  

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